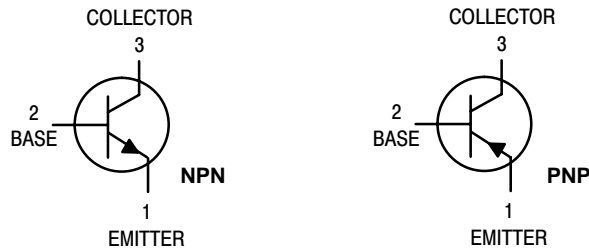


Amplifier Transistors



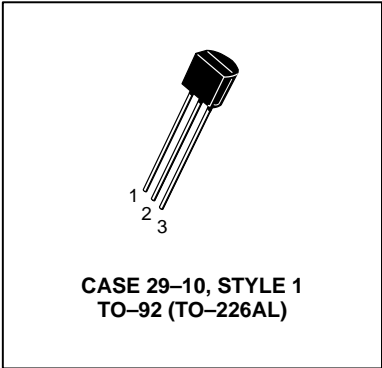
NPN
MPS650
MPS651 *
PNP
MPS750
MPS751 *

Voltage and current are negative for PNP transistors

*ON Semiconductor Preferred Devices

MAXIMUM RATINGS

Rating	Symbol	MPS650 MPS750	MPS651 MPS751	Unit
Collector–Emitter Voltage	V_{CE}	40	60	Vdc
Collector–Base Voltage	V_{CB}	60	80	Vdc
Emitter–Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous	I_C	2.0		Adc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625	5.0	mW mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5	12	Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		$^\circ\text{C}$



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 10 \text{ mAdc}, I_B = 0$)	MPS650, MPS750 MPS651, MPS751	$V_{(BR)CEO}$	40 60	— —	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	MPS650, MPS750 MPS651, MPS751	$V_{(BR)CBO}$	60 80	— —	Vdc
Emitter–Base Breakdown Voltage ($I_C = 0, I_E = 10 \mu\text{Adc}$)		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 60 \text{ Vdc}, I_E = 0$) ($V_{CB} = 80 \text{ Vdc}, I_E = 0$)	MPS650, MPS750 MPS651, MPS751	I_{CBO}	— —	0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ V}, I_C = 0$)		I_{EBO}	—	0.1	μAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle = 2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

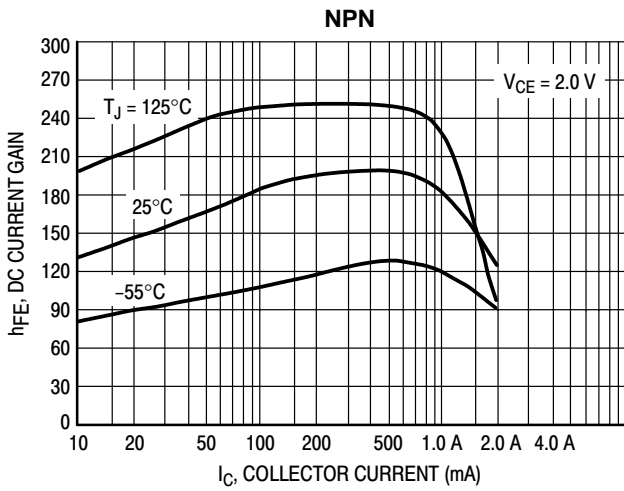
NPN MPS650 MPS651 PNP MPS750 MPS751

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (Continued)

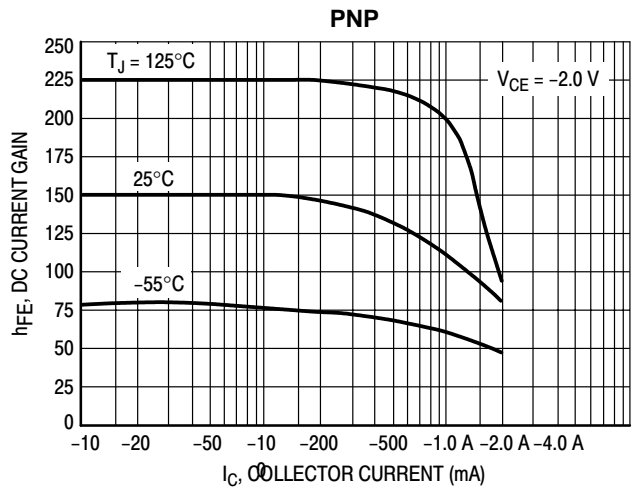
Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS⁽¹⁾				
DC Current Gain ($I_C = 50\text{ mA}$, $V_{CE} = 2.0\text{ V}$) ($I_C = 500\text{ mA}$, $V_{CE} = 2.0\text{ V}$) ($I_C = 1.0\text{ A}$, $V_{CE} = 2.0\text{ V}$) ($I_C = 2.0\text{ A}$, $V_{CE} = 2.0\text{ V}$)	h_{FE}	75 75 75 40	— — — —	—
Collector–Emitter Saturation Voltage ($I_C = 2.0\text{ A}$, $I_B = 200\text{ mA}$) ($I_C = 1.0\text{ A}$, $I_B = 100\text{ mA}$)	$V_{CE(sat)}$	— —	0.5 0.3	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ A}$, $V_{CE} = 2.0\text{ V}$)	$V_{BE(on)}$	—	1.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 1.0\text{ A}$, $I_B = 100\text{ mA}$)	$V_{BE(sat)}$	—	1.2	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ⁽²⁾ ($I_C = 50\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	75	—	MHz

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle = 2.0%.
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

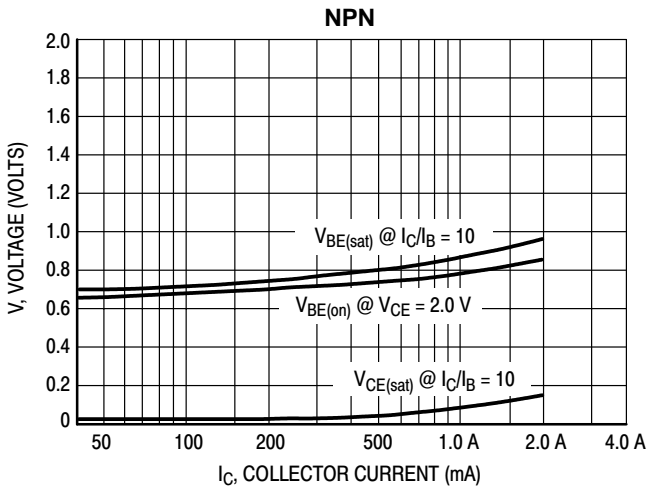
NPN MPS650 MPS651 PNP MPS750 MPS751



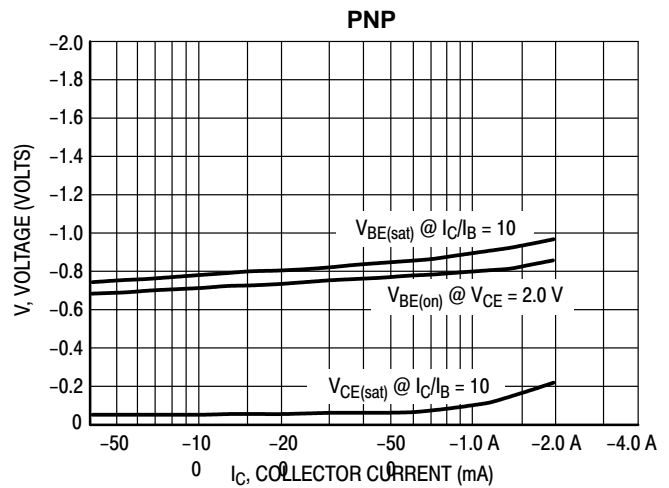
**Figure 1. MPS650, MPS651
Typical DC Current Gain**



**Figure 2. MPS750, MPS751
Typical DC Current Gain**

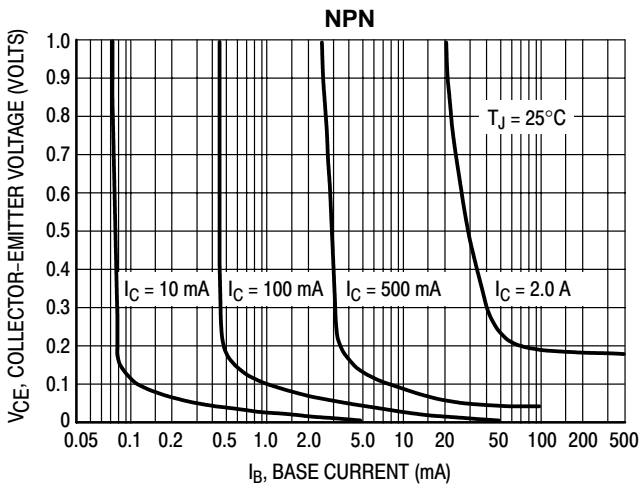


**Figure 3. MPS650, MPS651
On Voltages**

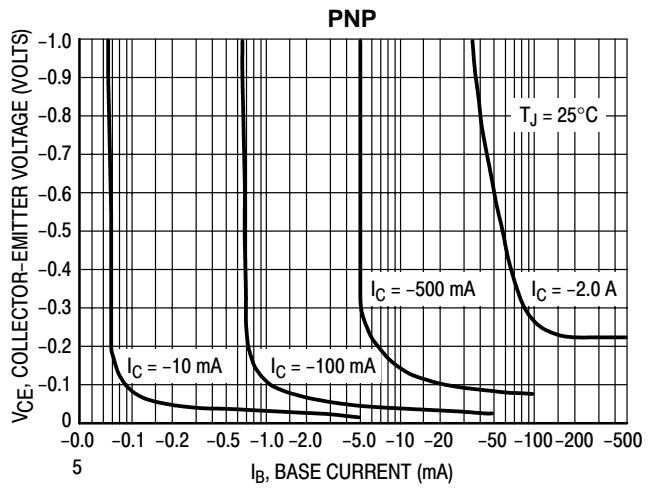


**Figure 4. MPS750, MPS751
On Voltages**

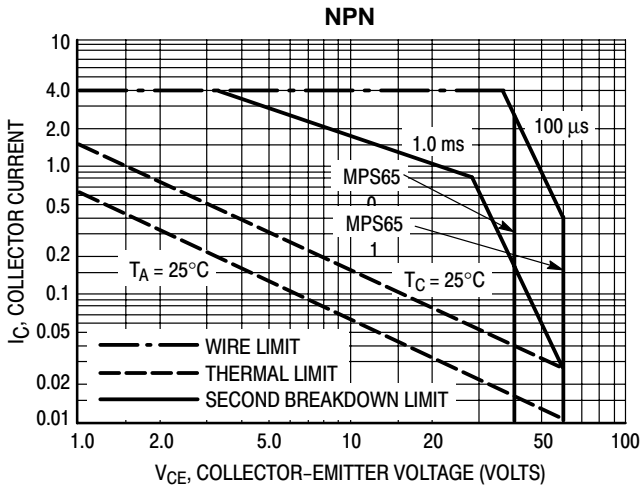
NPN MPS650 MPS651 PNP MPS750 MPS751



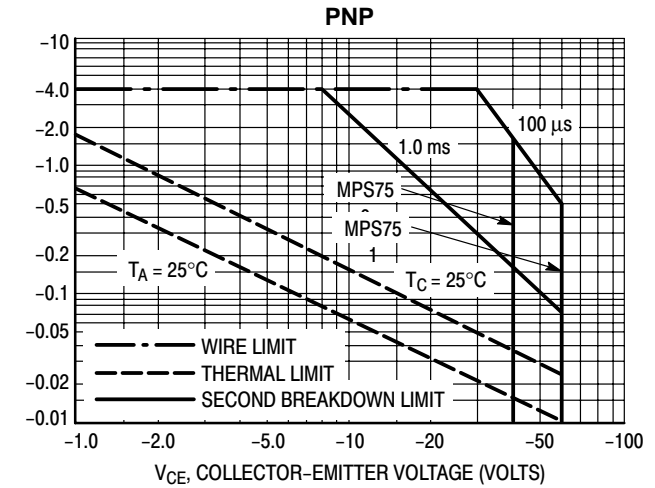
**Figure 5. MPS650, MPS651
Collector Saturation Region**



**Figure 8. MPS750, MPS751
Collector Saturation Region**



**Figure 6. MPS650, MPS651 SOA,
Safe Operating Area**

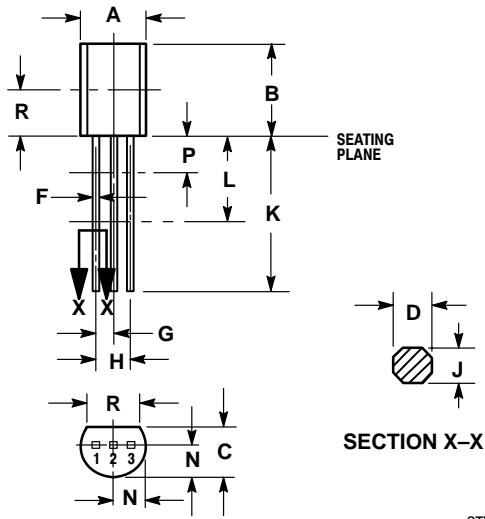


**Figure 7. MPS750, MPS751 SOA,
Safe Operating Area**

NPN MPS650 MPS651 PNP MPS750 MPS751

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-10
ISSUE AL



SECTION X-X

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---

Notes

Notes

NPN MPS650 MPS651 PNP MPS750 MPS751

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